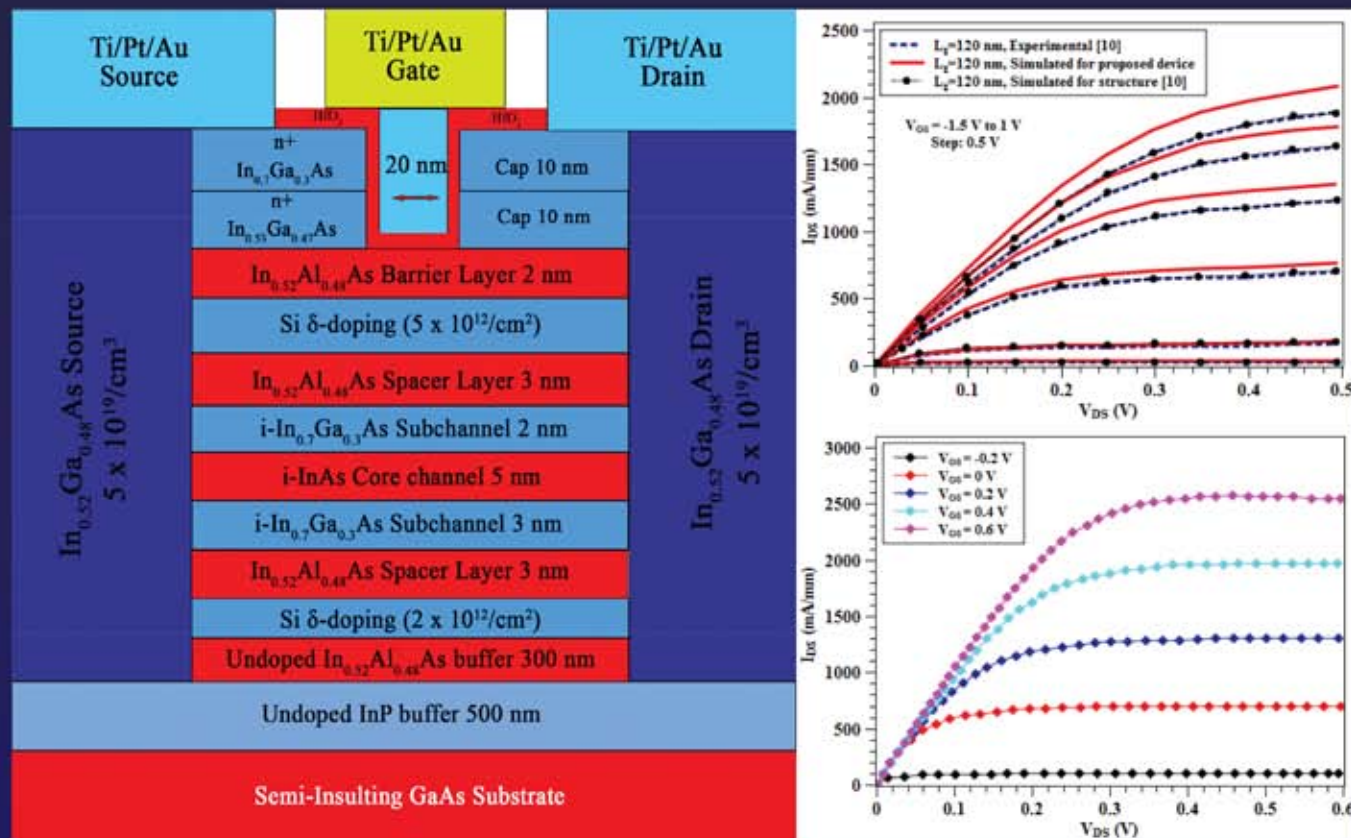


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 J. Ajayan, D. Nirmal, P. Mohankumar, L. Arivazhagan, M. Saravanan, and S. Saravanan

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